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(54) Title: METHODS FOR ENABLING CHEMICAL MECHANICAL POLISHING AND BONDING OF ALUMINUM-CONTAINING MATERIALS

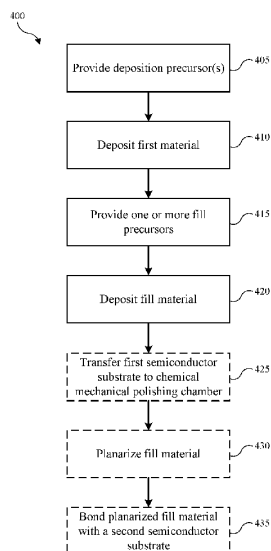


FIG. 4

(57) Abstract: Exemplary semiconductor processing methods may include depositing a first material on a first substrate. The first material may be characterized by a first average surface roughness greater than 5 Å. The methods may include depositing a fill material on the first material. The methods may include planarizing the fill material to form a planarized fill material. The planarized fill material may be characterized by a second average surface roughness less than the first average surface roughness. The methods may include bonding the planarized fill material to a second substrate.

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